

## 200V N-Channel Enhancement-Mode Power MOSFET

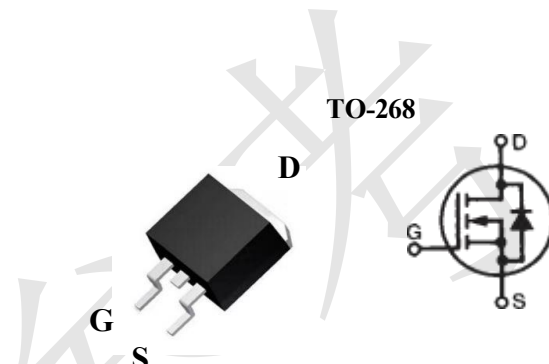
### General Features

- Enhancement Mode
- Linear MOSFET
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- High Power Density
- RoHS Compliant
- Avalanche Rated

$BV_{DSX}$	$R_{DS(ON)} (Max.)$	$I_{DSS(Min)}$
200V	30mΩ	80A

### Applications

- Suppressing Surge Current
- Start-up Circuits
- Converters
- Synchronous Rectification
- Constant Current Source
- Ramp Generators
- Current Regulators
- Protection Circuits
- Linear Amplifiers



### Ordering Information

Part Number	Package	Marking	Remark
AKG84C20LA	TO-268	84C20LA	Halogen Free

### Absolute Maximum Ratings

 $T_C=25^{\circ}C$  unless otherwise specified

Symbol	Parameter	AKG84C20LA	Unit
$V_{DSX}$	Drain-to-Source Voltage <sup>[1]</sup>	200	V
$V_{DGX}$	Drain-to-Gate Voltage <sup>[1]</sup>	200	V
$P_D$	Power Dissipation	520	W
	Derating Factor above 25°C	520	W/°C
$V_{GS}$	Gate-to-Source Voltage	±20	V
$T_L$	Soldering Temperature	300	°C
	Distance of 1.6mm from case for 10 seconds		
$T_J$ and $T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.